Three Phase Full Controlled Rectifier Bridge, B6C
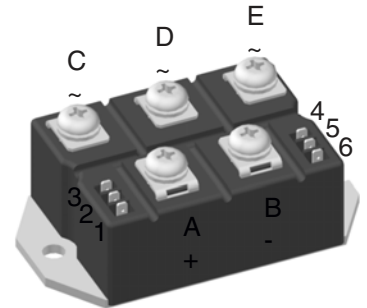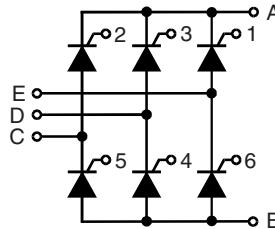
I_{dAVM} = 110/167 A
V_{RRM} = 1200-1600 V

Preliminary data

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type	
V	V		
1300	1200	VTO 110-12io7	VTO 175-12io7
1500	1400	VTO 110-14io7	VTO 175-14io7
1700	1600		VTO 175-16io7

Symbol	Test Conditions		Maximum Ratings VTO 110	VTO 175	
I_{dAV}	T_C = 85°C; module		110	167	A
I_{FRMS}, I_{TRMS}	per leg		58	89	A
I_{FSM}, I_{TSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	1150	1500	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	1230	1600	A
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	1000	1350	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	1070	1450	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	6600	11200	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	6280	10750	A^2s
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	5000	9100	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	4750	8830	A^2s
$(di/dt)_{cr}$	T_{VJ} = T_{VJM} repetitive, I_T = 50 A f = 400 Hz, t_p = 200 µs V_D = 2/3 V_{DRM}		150		A/µs
	I_G = 0.3 A, non repetitive di_G/dt = 0.3 A/µs, I_T = 1/3 • I_{dAV}		500		A/µs
$(dv/dt)_{cr}$	T_{VJ} = T_{VJM}; V_{DR} = 2/3 V_{DRM} R_{GK} = ∞; method 1 (linear voltage rise)		1000		V/µs
V_{RGM}			10		V
P_{GM}	T_{VJ} = T_{VJM} t_p = 30 µs		≤ 10		W
	I_T = I_{TAVM} t_p = 500 µs		≤ 5		W
	t_p = 10 ms		≤ 1		W
P_{GAVM}			0.5		W
T_{VJ}			-40...+125		°C
T_{VJM}			125		°C
T_{stg}			-40...+125		°C
V_{ISOL}	50/60 Hz, RMS t = 1 min		2500		V~
	I_{ISOL} ≤ 1 mA t = 1 s		3000		V~
M_d	Mounting torque (M6)		5-15		Nm
	Terminal connection torque (M6)		5-15		lb.in.
Weight	typ.		300		g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- UL registered E72873

Applications

- Input rectifier for PWM converter
- Input rectifier for switch mode power supplies (SMPS)
- Softstart capacitor charging

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

IXYS reserves the right to change limits, test conditions and dimensions.

20080227a

Symbol	Test Conditions		Characteristic Values			
			VTO 110	**VTO 175**		
I_R, I_D	$V_R = V_{RRM}$; $V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$	$\leq$	5		mA
		$T_{VJ} = 25°C$	$\leq$	0.3		mA
V_F, V_T	I_F, $I_T = 200$ A, $T_{VJ} = 25°C$		$\leq$ 1.75	1.57		V
V_{T0}	For power-loss calculations only		0.85	0.85		V
r_T	($T_{VJ} = 125°C$)		6	3.5		mΩ
V_{GT}	$V_D = 6$ V;	$T_{VJ} = 25°C$	$\leq$	1.5		V
		$T_{VJ} = -40°C$	$\leq$	1.6		V
I_{GT}	$V_D = 6$ V;	$T_{VJ} = 25°C$	$\leq$	100		mA
		$T_{VJ} = -40°C$	$\leq$	200		mA
V_{GD}	$T_{VJ} = T_{VJM}$;	$V_D = ^2/_3\, V_{DRM}$	$\leq$	0.2		V
I_{GD}	$T_{VJ} = T_{VJM}$;	$V_D = ^2/_3\, V_{DRM}$	$\leq$	5		mA
I_L	$I_G = 0.3$ A; $t_G = 30$ μs	$T_{VJ} = 25°C$	$\leq$	450		mA
	$di_G/dt = 0.3$ A/μs					
I_H	$T_{VJ} = 25°C$; $V_D = 6$ V; $R_{GK} = \infty$		$\leq$	200		mA
t_{gd}	$T_{VJ} = 25°C$; $V_D = ½\, V_{DRM}$		$\leq$	2		μs
	$I_G = 0.3$ A; $di_G/dt = 0.3$ A/μs					
R_{thJC}	per thyristor (diode); DC current		0.65	0.46		K/W
	per module		0.108	0.077		K/W
R_{thJH}	per thyristor (diode); DC current		0.8	0.55		K/W
	per module		0.133	0.092		K/W
d_S	Creeping distance on surface		10			mm
d_A	Creepage distance in air		9.4			mm
a	Max. allowable acceleration		50			m/s²

Fig. 1 Gate trigger characteristics

1: I_{GT}, $T_{VJ} = 125°C$
2: I_{GT}, $T_{VJ} = 25°C$
3: I_{GT}, $T_{VJ} = -40°C$
4: $P_{GAV} = 0.5$ W
5: $P_{GM} = 5$ W
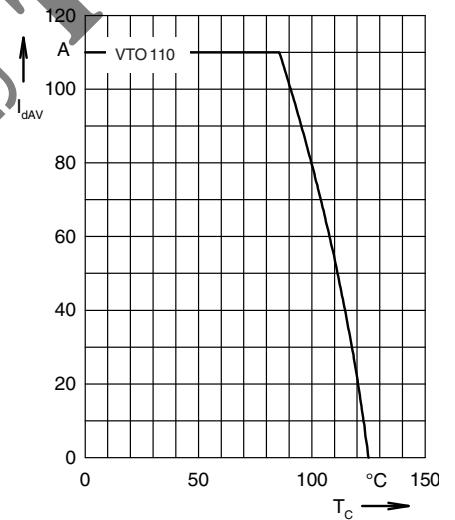6: $P_{GM} = 10$ W
I_{GD}, $T_{VJ} = 125°C$

Fig. 2 DC output current at case temperature
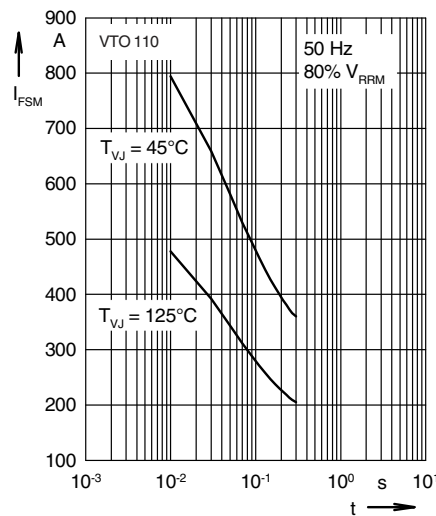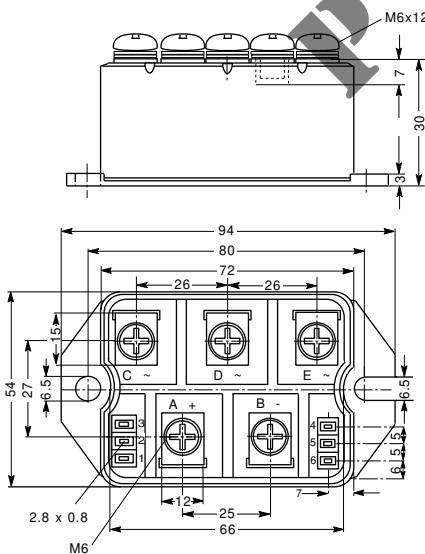
Dimensions in mm (1 mm = 0.0394")

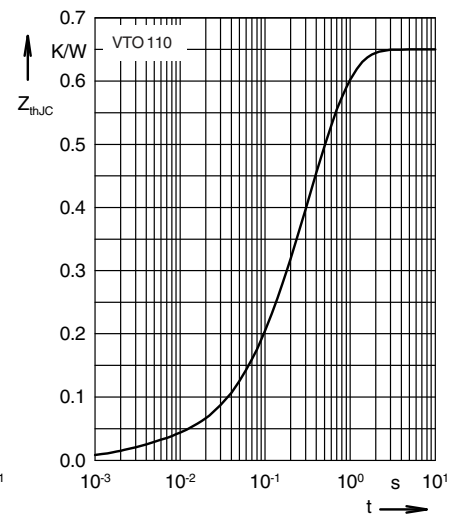Fig. 3 Surge overload current
I_{FSM}: Crest value, t: duration

Fig. 4 Transient thermal impedance junction to case (per leg)

IXYS reserves the right to change limits, test conditions and dimensions.

20080227a